

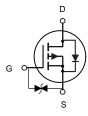
Description

The AO3485C uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

D S S G SOT-23-3L

General Features

 $V_{DS} = -20V \ I_D = -4.1A$ $R_{DS(ON)} < 45 m\Omega @ V_{GS} = -4.5V$ ESD Rating: 1500V HBM



Application

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AO3485C	SOT-23-3L	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±10	V
ID	Drain Current-Continuous	-4.1	A
Ірм	Drain Current-Pulsed (Note 1)	-30	A
P _D	Maximum Power Dissipation	1.4	W
Тл,Тэтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	89.3	°C/W



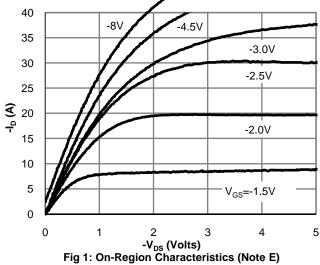
Electrical Characteristics (T_A=25°C unless otherwise noted)

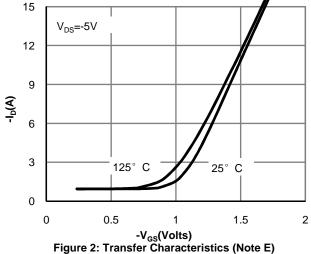
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Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} = 0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-0.35	-0.55	-0.9	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4A	-	34	45	mΩ
Drain-Source On-State Resistance		V _{GS} =-2.5V, I _D -4A	-	44	60	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D = -4A	8	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =-10V,V _{GS} =0V, F=1.0MHz	-	950	-	PF
Output Capacitance	Coss		-	165	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.0IVID2	-	120	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	12		nS
Turn-on Rise Time	t _r	V _{DD} =-10V,R _L =2. 5Ω	-	10		nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-4.5 V , R_{GEN} =3 Ω	-	19		nS
Turn-Off Fall Time	t _f		-	25		nS
Total Gate Charge	Qg	V _{DS} =-10V,I _D =-4A, V _{GS} =-4.5V	-	12		nC
Gate-Source Charge	Q _{gs}		-	1.4	-	nC
Gate-Drain Charge	Q_{gd}	VGS4.5V	-	3.6	-	nC
Drain-Source Diode Characteristics			•			-
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =4A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-4	Α
	•		•			

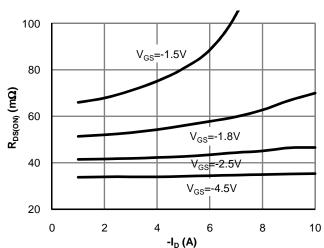
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics







-I_D (A) Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

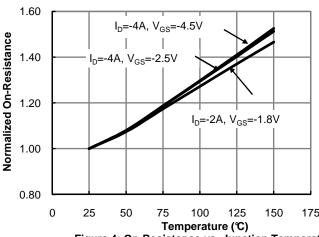


Figure 4: On-Resistance vs. Junction Temperature (Note E)

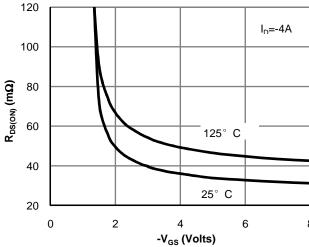


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

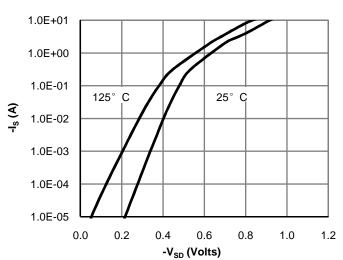
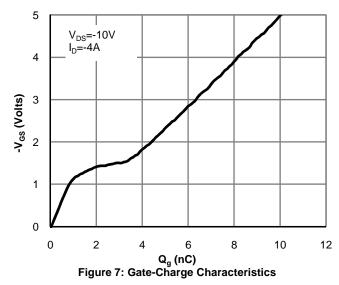
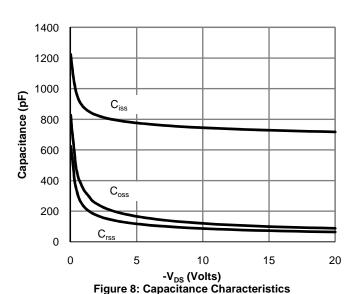
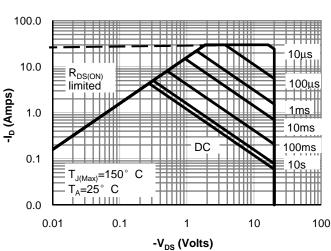


Figure 6: Body-Diode Characteristics (Note E)









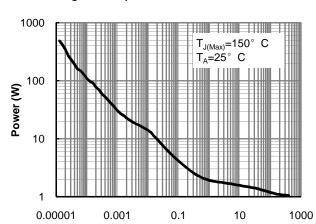


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Pulse Width (s)
Figure 10: Single Pulse Power Rating Junction-toAmbient (Note F)

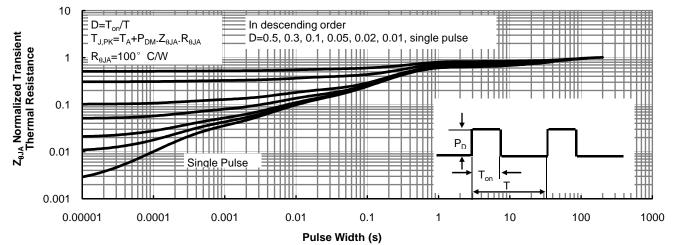
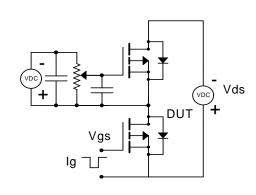
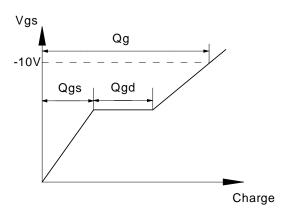


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

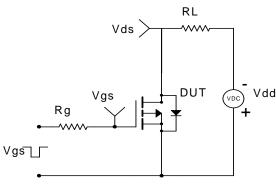


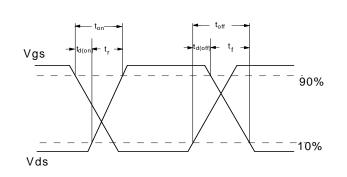
Gate Charge Test Circuit & Waveform



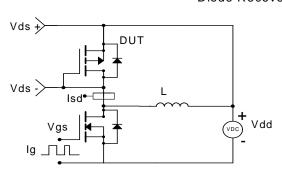


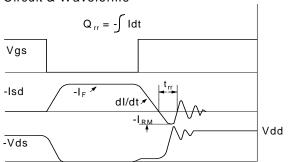
Resistive Switching Test Circuit & Waveforms



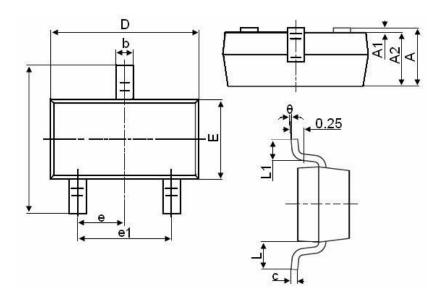


Diode Recovery Test Circuit & Waveforms





SOT-23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
Е	1.500	1.700	
E1	2.650	2.950	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



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